



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
2017	12mΩ @ V _{GS} = 10V	43.3A
60V	15mΩ @ V _{GS} = 4.5V	38.7A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

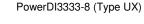
Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

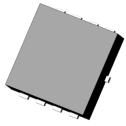
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.030 grams (Approximate)

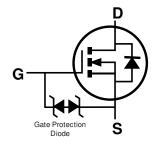
Pin1











Internal Schematic

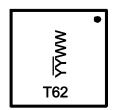
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6012LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape and Reel
DMT6012LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape and Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$		I _D	43.3 34.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	170	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	40	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	170	Α	
Avalanche Current, L = 0.1mH	I _{AS}	23.7	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	28.1	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.95	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ hetaJA}$	64	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_{D}	33.78	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	3.7	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

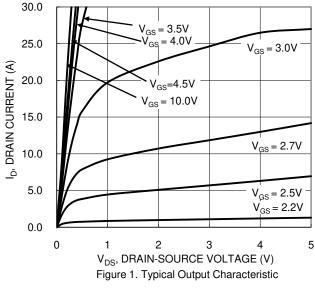
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	8.2	12	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Diain-Source On-Nesistance	R _{DS(ON)}	_	11.2	15	11152	$V_{GS} = 4.5V, I_D = 12.5A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	1522	_		$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	352		pF		
Reverse Transfer Capacitance	C_{rss}	_	27.5	_			
Gate Resistance	R_{g}	_	1.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	10.7				
Total Gate Charge (V _{GS} = 10V)	Q_g	_	22.2	_			
Gate-Source Charge	Qgs	_	3.3		nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Q_{gd}	_	4.2	_			
Turn-On Delay Time	t _{D(ON)}	_	4.4	_			
Turn-On Rise Time	t _R	_	6.7	_	no	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t _{D(OFF)}		25.5	_	ns	$R_g = 6\Omega$, $I_D = 10A$	
Turn-Off Fall Time	t _F	_	12.5	_			
Reverse Recovery Time	t _{RR}	_	25.8	_	ns	1 10A di/dt 100A/va	
Reverse Recovery Charge	erse Recovery Charge Q_{RR} — 15.1 — nC $I_F = 107$		$_{F} = 10A$, di/dt = 100A/ μ s				

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Solution in the stance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





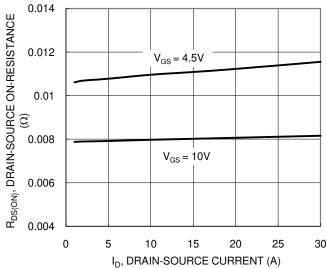
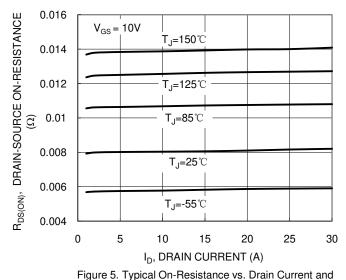
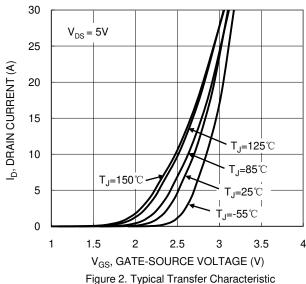


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



Junction Temperature



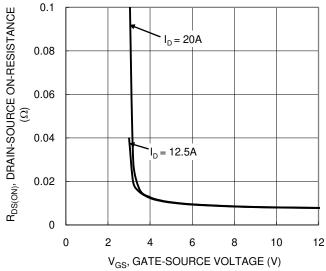


Figure 4. Typical Transfer Characteristic

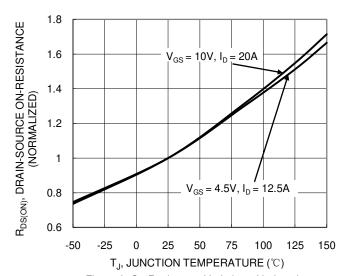


Figure 6. On-Resistance Variation with Junction Temperature



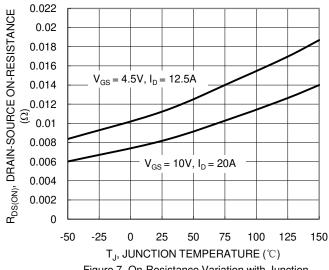
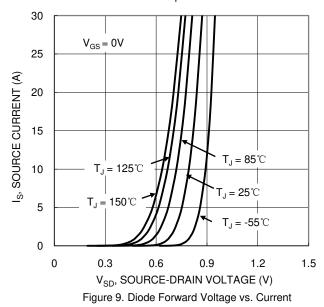


Figure 7. On-Resistance Variation with Junction Temperature



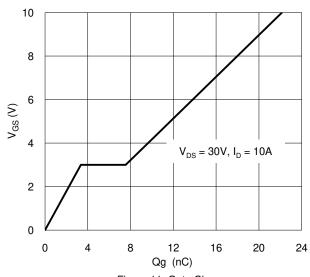


Figure 11. Gate Charge

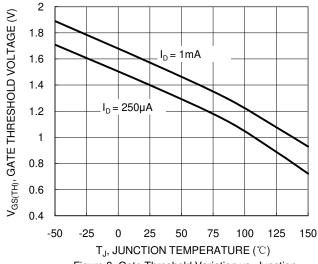
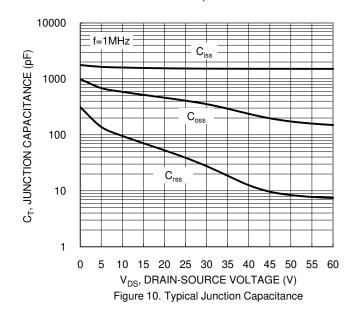
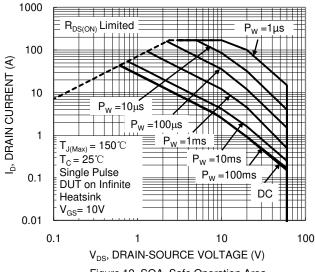


Figure 8. Gate Threshold Variation vs. Junction Temperature







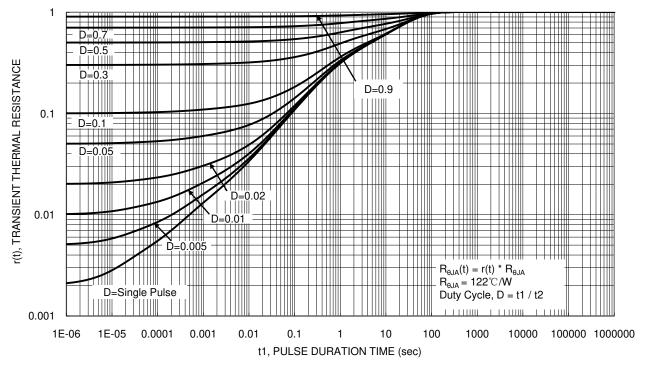


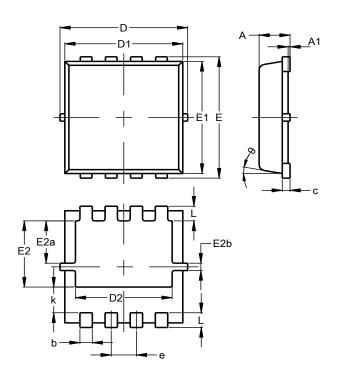
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

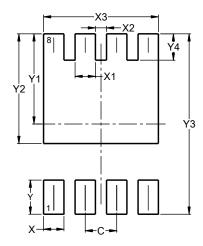


PowerDI3333-8 (Type UX)					
Dim	Min	Min Max Typ			
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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